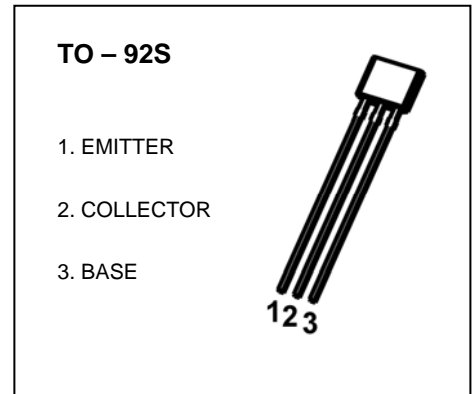


FTC2389S TRANSISTOR (NPN)

FEATURES

- High Breakdown Voltage.
- Complements the FTA1038S.



MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CB0}	Collector-Base Voltage	120	V
V _{CEO}	Collector-Emitter Voltage	120	V
V _{EBO}	Emitter-Base Voltage	5	V
I _C	Collector Current	50	mA
P _C	Collector Power Dissipation	300	mW
R _{θJA}	Thermal Resistance From Junction To Ambient	417	°C/W
T _j	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55~+150	°C

ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =50μA, I _E =0	120			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =1mA, I _B =0	120			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =50μA, I _C =0	5			V
Collector cut-off current	I _{CBO}	V _{CB} =100V, I _E =0			0.5	μA
Emitter cut-off current	I _{EBO}	V _{EB} =4V, I _C =0			0.5	μA
DC current gain	h _{FE}	V _{CE} =6V, I _C =2mA	180		560	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =10mA, I _B =1mA			0.5	V
Collector output capacitance	C _{ob}	V _{CB} =12V, I _E =0, f=1MHz		2.5		pF
Transition frequency	f _T	V _{CE} =12V, I _C =2mA, f=100MHz		140		MHz

CLASSIFICATION OF h_{FE}

RANK	R	S
RANGE	180-390	270-560